L	Hits	Search Text	DB	Time stamp
Number 1	86	(tec or thermal near2 expansion near2 coefficient).AB. and 117/\$4.ccls.	USPAT; US-PGPUB;	2004/09/28 11:13
		coefficient).AB. and 117794.ccis.	EPO; JPO; DERWENT; IBM TDB	11.13
2	2088	<pre>(tec or thermal near2 expansion near2 coefficient) near15 (warp\$5 or bow\$4)</pre>	USPAT; US-PGPUB; EPO; JPO;	2004/09/28 11:14
3	45	<pre>(tec or thermal near2 expansion near2 coefficient) near15 (warp\$5 or bow\$4)</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/09/28 11:36
		same epitax\$5	EPO; JPO; DERWENT; IBM_TDB	2004/09/28
4	162	<pre>(tec or thermal near2 expansion near2 coefficient) near15 (warp\$5 or bow\$4) and epitax\$5</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	11:37
5	26	(tec or thermal near2 expansion near2 coefficient) near15 (warp\$5 or bow\$4) near10 (reduc\$5) and epitax\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/28 11:56
6	1	(gaas or gallium near2 arsenide) near10 epitax\$5 near10 temperature near10 "1000"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/28 11:57
7	43	(gaas or gallium near2 arsenide) near10 temperature near10 "1000"	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/28 11:59
8	410	(titanium or tungsten or tantalum or molybdenum or cobalt or nickel) near2 silicide near10 deposit\$5 near10 temperature	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/28 12:02
9	2	(titanium or tungsten or tantalum or molybdenum or cobalt or nickel) near2 silicide near10 deposit\$5 near10 temperature near5 "650"	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/28 12:01
10	9	(titanium or tungsten or tantalum or molybdenum or cobalt or nickel) near2 silicide near10 deposit\$5 near10 temperature near5 "600"	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/09/28 12:02
11	1	(titanium or tungsten or tantalum or molybdenum or cobalt or nickel) near2 silicide near10 deposit\$5 near10 temperature near5 "550"	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/28 12:02
12	214	((titanium or tungsten or tantalum or molybdenum or cobalt or nickel) near2 silicide near10 deposit\$5 near10 temperature) and @py<2001	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/28 14:32
13	2228	(sin or silicon adj nitride) near10 deposit\$5 near10 temperature	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/28 14:34
14	982	((sin or silicon adj nitride) near10 deposit\$5 near10 temperature) and @py<2000	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/09/28

			**************************************	2004/02/22
15	1639	(sin or silicon adj nitride) near10	USPAT; US-PGPUB;	2004/09/28 14:34
		deposit\$5 near5 temperature	EPO; JPO;	14.34
			DERWENT;	
			IBM TDB	
16	1296	(sin or silicon adj nitride) near5	USPAT;	2004/09/28
		deposit\$5 near5 temperature	US-PGPUB;	14:34
			EPO; JPO; DERWENT;	
			IBM TDB	
17	666	(sin or silicon adj nitride) near5	USPAT;	2004/09/28
		deposit\$5 near2 temperature	US-PGPUB;	14:36
	1		EPO; JPO;	
			DERWENT; IBM TDB	
18	283	((sin or silicon adj nitride) near5	USPAT;	2004/09/28
10	203	deposit\$5 near2 temperature) and @py<2000	US-PGPUB;	14:35
		, , , , , , , , , , , , , , , , , , ,	EPO; JPO;	
			DERWENT;	
		12 12 12 12 12 12 12 12 12 12 12 12 12 1	IBM_TDB	2004/09/28
19	0	(sin or silicon adj nitride) near5 deposit\$5 near2 temperature near5 "1050"	USPAT; US-PGPUB;	14:36
		debosichs Hears remberarate Hears 1030	EPO; JPO;	
			DERWENT;	
	i.		IBM_TDB	
20	2	(sin or silicon adj nitride) near5	USPAT;	2004/09/28
		deposit\$5 near2 temperature near5 "1000"	US-PGPUB; EPO; JPO;	14:36
			DERWENT;	
			IBM TDB	
21	140	(sin or silicon adj nitride) near5	USPAT;	2004/09/28
		deposit\$5 near2 temperature near5 high	US-PGPUB;	14:40
			EPO; JPO; DERWENT;	
			IBM TDB	
22	2.0	thermal near10 (sin or silicon near2	USPAT;	2004/09/28
		nitride) same (jig or boat)	US-PGPUB;	14:43
			EPO; JPO;	
			DERWENT; IBM TDB	
23	3	"0713245"	USPAT;	2004/09/28
23		0713243	US-PGPUB;	14:43
			EPO; JPO;	
			DERWENT;	
		WE44444	IBM_TDB	2004/09/28
24	8	"713245"	USPAT; US-PGPUB;	14:44
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
25	98	(sin or silicon near2 nitride) near10	USPAT;	2004/09/28
		temperature near2 ("1100" or "1000" or "1050" or "1200")	US-PGPUB; EPO; JPO;	14:43
		1050 Of 1200 )	DERWENT;	
			IBM_TDB	
26	47	layered near2 substrate near10 (sapphire	USPAT;	2004/09/28
		or "al.sub.2o.sub.3")	US-PGPUB;	14:56
			EPO; JPO; DERWENT;	
			IBM TDB	
27	27	(sin or silicon near2 nitride or silicon	USPAT;	2004/09/28
-		near2 oxide or "sio.sub.2") near10	US-PGPUB;	15:26
	9	deposit\$5 near2 temperature near5 ("850"	EPO; JPO;	
	वर्ते सर्वे	or "900" or "950" or "800")	DERWENT;	
120	142	mocvd near10 (gan or gallium adj nitride)	<pre>IBM_TDB USPAT;</pre>	2004/09/28
28	<u>142</u>	near10 (gan or gallium adj nitride)	US-PGPUB;	15:28
			EPO; JPO;	
			DERWENT;	
	1		IBM TDB	

29	12	mocvd near10 (gan or gallium adj nitride)	USPAT;	2004/09/28
		near10 epitax\$6 near10 (temperature)	US-PGPUB; EPO; JPO;	15:29
			DERWENT;	
			IBM TDB	
30	0	(mocvd or movpe) near10 (gan or gallium	USPAT;	2004/09/28
30		adj nitride) near10 (temperature) same	US-PGPUB;	15:29
		epitax4	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
31	34		USPAT;	2004/09/28
		adj nitride) near10 (temperature) same	US-PGPUB;	17:09
		epitax\$4	EPO; JPO;	
			DERWENT;	
20		and trame or	IBM_TDB   USPAT;	2004/09/28
32	0	udea near2 tetsuzo.in. and (warp\$ or   bow\$4)	US-PGPUB;	17:10
		DOW\$4)	EPO; JPO;	17.10
		·	DERWENT;	
			IBM TDB	
33	12	ueda near2 tetsuzo.in. and (warp\$ or	USPAT;	2004/09/28
1		bow\$4)	US-PGPUB;	17:10
1	1		EPO; JPO;	
1			DERWENT;	
			IBM_TDB	0004/00/00
_	353	olsen.in. and bow\$3	USPAT;	2004/02/09
			US-PGPUB;	18:08
1			EPO; JPO; DERWENT;	
			IBM TDB	
1_	2	olsen.in. and bow\$3 near10 wafer	USPAT;	2004/02/09
ł <sup>-</sup>		Olsen.in. and powys hearts warer	US-PGPUB;	18:09
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	1280	bow\$3 near10 wafer	USPAT;	2004/02/09
			US-PGPUB;	18:09
			EPO; JPO;	
			DERWENT;	1
		10 5 (1.1.1	IBM_TDB USPAT;	2004/02/10
_	38	bow\$3 near10 wafer same nitride	US-PGPUB;	11:05
			EPO; JPO;	11.05
			DERWENT;	
			IBM TDB	
_	96	bow\$3 near10 wafer near10 flat\$4	USPAT;	2004/02/10
			US-PGPUB;	13:47
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/02/10
] -	687	deposit\$ near15 wafer near10 flat\$4	USPAT;	2004/02/10
			US-PGPUB; EPO; JPO;	13:30
			DERWENT;	
			IBM TDB	
_	70	deposit\$ near15 wafer near10 (flatten or	USPAT;	2004/02/10
1	, ,	flattening or flattens)	US-PGPUB;	13:50
		'	EPO; JPO;	
1			DERWENT;	
1			IBM_TDB	1
-	3	5562770.URPN.	USPAT	2004/02/10
		/#2450250# / #2000574# / #2004022# /	TICDAE	13:53
-	12	("3458369"   "3808674"   "3821033"	USPAT	2004/02/10 13:54
1		"3997368"   "4079506"   "4159214"   "4415373"   "4631804"   "4805071"		13:34
		"4415373"   "4631804"   "4805071"     "4830984"   "5158907"   "5319570").PN.		
_	225	direct near5 heat\$4 and 117/\$.ccls.	USPAT;	2004/02/10
1	, ~~~	all too hears heavy and lifty.com.	US-PGPUB;	14:32
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	

_	66	direct near5 heat\$4 and 117/\$.ccls. and	USPAT;	2004/02/10
		(chemical adj vapor adj deposition or	US-PGPUB;	14:36
	1	cvd)	EPO; JPO;	
	Ì		DERWENT;	·
			IBM_TDB	2004/02/10
-	1911	without near4 heat near2 sink	USPAT;	2004/02/10
			US-PGPUB;	14:36
1			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	77	, , , , , , , , , , , , , , ,	USPAT;	2004/02/10
		or chemical adj vapor adj deposition)	US-PGPUB;	14:38
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	2004/20/12
-	6		USPAT;	2004/02/10
		or chemical adj vapor adj deposition))	US-PGPUB;	14:37
	1	and 117/\$.ccls.	EPO; JPO;	
			DERWENT;	
	1	[	IBM_TDB	0004/00/20
-	5	(without near4 heat near2 sink) same	USPAT;	2004/02/10
	1	(direct\$4 near2 heat\$4) and (cvd or	US-PGPUB;	14:38
	[	chemical adj vapor adj deposition)	EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	38	ueda near2 tetsuzo.in.	USPAT;	2004/02/23
	1		US-PGPUB;	11:18
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	
-	0	ammonia near10 partial near2 pressure	USPAT;	2004/02/23
		same (anneal\$ or heat near2 treat\$ or	US-PGPUB;	11:20
		rapid near2 thermal or rta or rtp) same	EPO; JPO;	
		(p\$1type)	DERWENT;	
			IBM_TDB	l
_	2	I -	USPAT;	2004/02/23
		or heat near2 treat\$ or rapid near2	US-PGPUB;	11:20
		thermal or rta or rtp) same (p\$1type)	EPO; JPO;	
			DERWENT;	
-			IBM_TDB	
-	3		USPAT;	2004/02/23
		or heat near2 treat\$ or rapid near2	US-PGPUB;	11:21
		thermal or rta or rtp) same resistiv\$	EPO; JPO;	
		·	DERWENT;	
			IBM_TDB	
-	1	titanium near2 silicide near10 sputter	USPAT;	2004/09/20
	[	near2 temperature	US-PGPUB;	17:02
	1		EPO; JPO;	
	1		DERWENT;	
	1		IBM_TDB	
-	8	(titanium near2 silicide or tisi) same	USPAT;	2004/09/20
	[	sputter near12 temperature	US-PGPUB;	17:02
	1		EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
-	1487	wafer near10 bow\$5	USPAT;	2004/09/27
	1		US-PGPUB;	16:21
	1		EPO; JPO;	
	]		DERWENT;	
	1		IBM_TDB	0004/50/05
-	40	'	USPAT;	2004/09/27
		near2 nitride)	US-PGPUB;	16:47
]	1		EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	224	(wafer near10 bow\$5) same flat\$4	USPAT;	2004/09/27
			US-PGPUB;	16:58
			EPO; JPO;	
	ŀ		DERWENT;	
l	I	1	IBM_TDB	

_	2580	(sin or silicon near2 nitride) near10 (deposit\$5 or grow\$4) near10 temperature	USPAT; US-PGPUB; EPO; JPO;	2004/09/27 17:00
			DERWENT; IBM TDB	
_	28	(sin or silicon near2 nitride) near10	USPAT;	2004/09/27
		(deposit\$5 or grow\$4) near10 temperature	US-PGPUB;	17:25
		near10 "650"	EPO; JPO; DERWENT;	
			IBM_TDB	
_	119		USPAT; US-PGPUB;	2004/09/27 17:27
		layered near10 substrate	EPO; JPO;	17.27
			DERWENT;	
	0.4	/ 11i.m nasm2 mitmide) near10	IBM_TDB USPAT;	2004/09/27
_	84	(gan or gallium near2 nitride) near10   layered near2 substrate	US-PGPUB;	17:36
			EPO; JPO;	
			DERWENT; IBM TDB	
_	17		USPAT;	2004/09/27
		layered near2 substrate near10 (sapphire	US-PGPUB;	17:35
		or "al.sub.2o.sub.3")	EPO; JPO; DERWENT;	
	3-		IBM_TDB	
-	14		USPAT; US-PGPUB;	2004/09/27
		layered adj substrate	EPO; JPO;	17.30
			DERWENT;	
	100	in will warm (man an mallitum add	IBM_TDB USPAT;	2004/09/27
_	109	epitaxial near5 (gan or gallium adj nitride) near10 (deposit\$5 or grow\$5)	US-PGPUB;	17:39
		near5 temperature	EPO; JPO;	
			DERWENT; IBM TDB	
_	25		USPĀT;	2004/09/27
		nitride) near10 (deposit\$5 or grow\$5)	US-PGPUB; EPO; JPO;	17:44
		near5 temperature same MOCVD	DERWENT;	
			IBM_TDB	2004/09/27
-	332	thermal near2 expansion near10 (gan or gallium near2 nitride) near2 coefficient	USPAT; US-PGPUB;	17:45
		garram nour mours	EPO; JPO;	
			DERWENT; IBM TDB	
_	94	thermal near2 expansion near2 (gan or	USPAT;	2004/09/27
		gallium near2 nitride) near2 coefficient	US-PGPUB;	17:54
			EPO; JPO; DERWENT;	
			IBM_TDB	0004/00/05
-	120	(gan or gallium near2 nitride) same bow\$5	USPAT; US-PGPUB;	2004/09/27 18:01
			EPO; JPO;	-3.02
			DERWENT;	
_	18	(gan or gallium near2 nitride) same bow\$5	IBM_TDB USPAT;	2004/09/27
		near5 substrate	US-PGPUB;	17:59
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	146		USPAT;	2004/09/28
		near5 temperature	US-PGPUB; EPO; JPO;	11:02
			DERWENT;	
			IBM TDB	